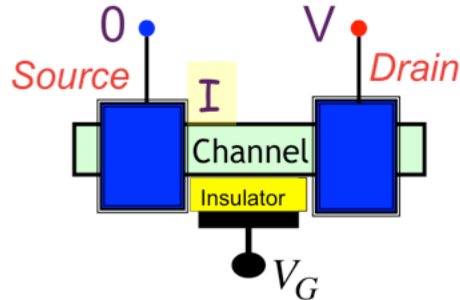


2.8. Quantum Capacitance

$$N = \int_{-\infty}^{+\infty} dE D(E - U) f_0(E) \quad (\text{A})$$

$$U = U_0(N - N_0) + b(-qV_G) \quad (\text{B})$$



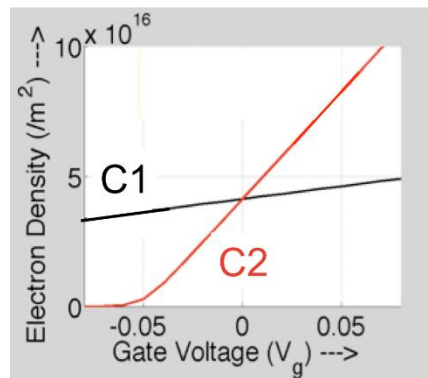
2.8a. The result that the electron density can be changed a gate voltage ~ 60 mV is obtained under the assumption that

- (a) $b=1$ in Eq.(B)
- (b) U_0 is negligible in Eq.(B)
- (c) The non-degenerate approximation for the Fermi function can be used in Eq.(A)
- (d) All three above, namely, (a), (b) and (c)
- (e) Only (a) and (c)

2.8b. The plots C1, C2 for electron density versus gate voltage solving Eqs.(A,B), with all the same parameters, except uses $U_0 \neq 0$.

Consider the following statements:

- (1) Plot C2 was obtained with $U_0=0$
- (2) Plot C1 was obtained with $U_0 \neq 0$
- (3) The quantum capacitance is proportional to
- (4) The quantum capacitance is proportional to



voltage were obtained by that one uses $U_0=0$ and one

the slope of C2
the slope of C1.

- (a) Only statement 3 is correct
- (b) Only statement 4 is correct
- (c) Only statements 1, 2 and 3 are correct
- (d) Only statements 1, 2 and 4 are correct
- (e) None of the above